



HUNIN ELECTRONICS CORP.

PRODUCTION SPECIFICATION

PRODUCT LINE : PHOTO TRANSISTOR

TITLE : HI-T420

1. GENERAL DESCRIPTION

The HI-T420 is a high sensitivity NPN silicon phototransistor mounted in clear epoxy side looking package.

The clear epoxy side looking package system is designed to optimize the mechanical resolution coupling efficiency, cost and reliability.

2. FEATURE.

- 1) Side looking package.
- 2) Good linearity.
- 3) Wide band of collector current.
- 4) Stable characteristics.
- 5) High reliability.
- 6) Suitable for HI-I300 or HI-I440 series.

3. ABSOLUTE MAXIMUM RATINGS.

(Ta=25 °C)

Parameter	Symbol	Ratings	Unit
Collector-emitter voltage	V _{CEO}	30	V
Emitter-collector voltage	V _{ECO}	5	V
Collector current	I _C	20	mA
Power dissipation	P _D	100	mW
Operating temperature	T _{opr}	-40 ~ +90	°C
Storage temperature	T _{stg}	-40 ~ +90	°C
Soldering temperature *1	T _{sol}	260(within 3 seconds)	°C

*1. Soldering part of lead: up to 2mm from the body of the device.

4. ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25 °C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Light Current	I _{CEL}	V _{ce} =5V, E _v =1000Lux	2	5		mA
Dark current	I _{CEO}	V _{ce} =10V, E _e =0			100	nA
Collector-Emitter saturation voltage	V _{CE(s)}	I _c =0.5mA, E _e =20mW/cm ²			0.4	V
Response time (Rise)	t _r	V _{ce} =30V, I _c =800μA R _L =1kΩ		5		usec
Response time (Fall)	t _f			5		usec
Peak wavelength sensitivity	λ _P			880		nm
Spectral Sensitivity	λ		450 ~ 1050			nm
Angle Sensitivity at 50%	θ			±30		deg.



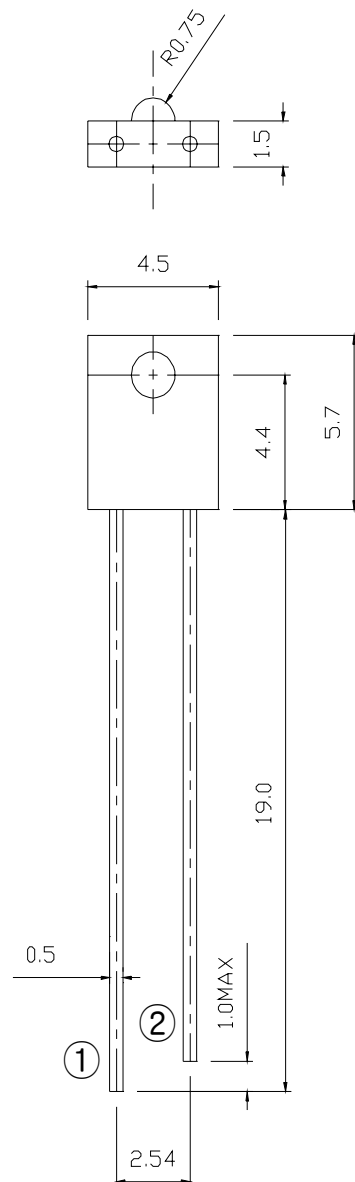
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5. DIMENSION



*Note

- 1.All dimension in "mm"
- 2.An epoxy meniscus may extend about "1.00" down the leads.
- 3.Tolerance ± 0.2 unless specified.
- 4.Electrode:
 - 1.Emitter
 - 2.Collector



